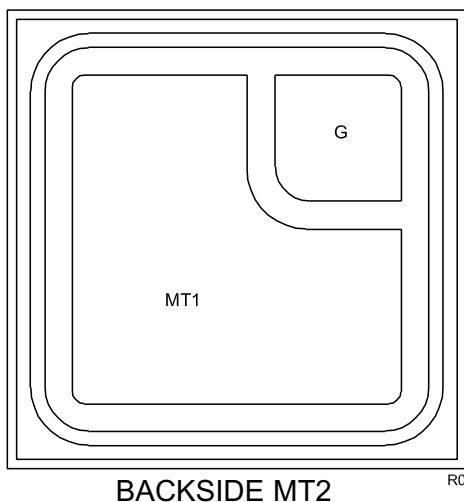


PROCESS DETAILS

Process	GLASS PASSIVATED MESA
Die Size	130 MILS x 130 MILS
Die Thickness	8.6 MILS \pm 0.6 MILS
MT1 Bonding Pad Area	99 MILS x 49 MILS
Gate Bonding Pad Area	34 MILS x 34 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

624

PRINCIPAL DEVICE TYPES

CQ220-12B Series

CQDD-12M Series

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

R0 (05-MAY 2005)